

## SAM<sup>TM</sup> Data Sheet SAM-3000-33-10ps-x, $\lambda$ = 3000 nm

Laser wavelength  $\lambda = 3000 \text{ nm}$ 

High reflection band  $\lambda = 2000 ... 3400 \text{ nm}$ 

Absorbance  $A_0 = 33 \%$  Modulation depth  $\Delta R = 18 \%$  Non-saturable loss  $A_{ns} = 15 \%$ 

Saturation fluence  $\Phi_{\text{sat}} = 70 \text{ }\mu\text{J/cm}^2$ 

Relaxation time constant  $\tau \sim 10 \text{ ps}$ 

Damage threshold  $\Phi = 1 \text{ mJ/cm}^2$ 

Chip area 4.0 mm x 4.0 mm; other dimensions on request

Chip thickness 625 µm

Design The SAM use a gold mirror

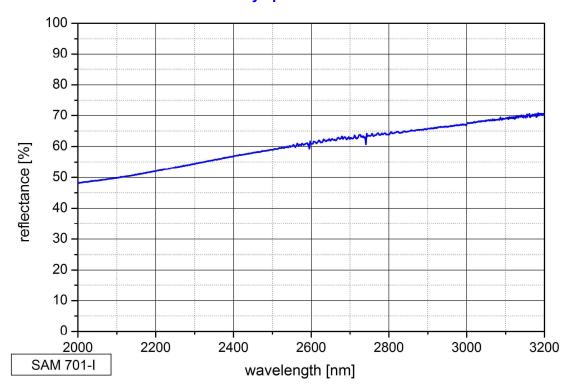
The laser beam goes through the AR coated GaAs wafer

Mounting option **x** denotes the type of mounting as follows:

x = 0 unmounted

x = 12.7 g glued on a gold plated Cu-cylinder with 12.7 mm  $\varnothing$ x = 25.4 g glued on a gold plated Cu-cylinder with 25.4 mm  $\varnothing$ 

## Low intensity spectral reflectance





## Reverse design of the SAM-3000-33-1ps-x

